

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	7875	bpsg same (oxide or "silicon oxide" or SiO or "SiO.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L2	4572	("silicon nitride" or SiN or "Si.sub.3N.sub.4") and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L3	1509	@ad<=19970204 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	1450	semiconductor and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	1422	substrate and 4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L6	578	capacitor and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB